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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete If Known	
Application Number	10/796,111
Filing Date	March 20, 2004
First Named Inventor	Dean A. Klein
Art Unit	2818
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0959/P959

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
DL	AA	US-6,673,648	01/06/2004	Lowrey	

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Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]-Number[4]-Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. [1] Applicant's unique citation designation number (optional). [2] See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]

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Examiner: Thao M. Luu Date: 10/28/04

PTO/SB/08A (10-01)
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 13

Complete if Known	
Application Number	10/796,111
Filing Date	March 10, 2004
First Named Inventor	Dean A. Klein
Art Unit	2818
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0959/P0959

U.S. PATENT DOCUMENTS

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PL	AA	2002/0000666	1/2002	Kozicki et al.	
	AB	2002/0072188	6/2002	Gilton	
	AC	2002/0106849	08/2002	Moore	
	AD	2002/0123169	09/2002	Moore et al.	
	AE	2002/0123170	09/2002	Moore et al.	
	AF	2002/0123248	09/2002	Moore et al.	
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	AH	2002/0132417	09/2002	Li	
	AI	2002/0160551	10/2002	Harshfield	
	AJ	2002/0163828	11/2002	Krieger et al.	
	AK	2002/0168852	11/2002	Harshfield et al.	
	AL	2002/0190289	12/2002	Harshfield et al.	
	AM	2003/0001229	01/2003	Moore et al.	
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	AP	2003/0038301	02/2003	Moore	
	AQ	2003/0043631	03/2003	Gilton et al.	
	AR	2003/0045049	03/2003	Campbell et al.	
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	AU	2003/0047772	03/2003	Li	
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	AW	2003/0049912	03/2003	Campbell et al.	
	AX	2003/0068861	04/2003	Li	
	AY	2003/0068862	04/2003	Li	
	AZ	2003/0095426	05/2003	Hush et al.	
	AA1	2003/0096497	05/2003	Moore et al.	
	AB1	2003/0107105	06/2003	Kozicki	
	AC1	2003/0117831	06/2003	Hush	
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	AE1	2003/0137869	07/2003	Kozicki	
	AF1	2003/0143782	07/2003	Gilton et al.	
	AG1	2003/0155589	08/2003	Campbell et al.	
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	AI1	2003/0156447	08/2003	Kozicki	
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	AK1	2003/0209728	11/2003	Kozicki et al	
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	AN1	3,622,319	11/1971	Sharp	
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	AQ1	4,312,938	1/1982	Drexler, et al.	
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Sheet 2 of 13

Complete if Known	
Application Number	10/796,111
Filing Date	March 10, 2004
First Named Inventor	Dean A. Klein
Art Unit	2818
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0959/P0959

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 3 of 13

Complete if Known	
Application Number	10/796,111
Filing Date	March 10, 2004
First Named Inventor	Dean A. Klein
Art Unit	2818
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0959/P0959

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	4	of	13

Complete if Known	
Application Number	10/796,111
Filing Date	March 10, 2004
First Named Inventor	Dean A. Klein
Art Unit	2818
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0959/P0959

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	AJ6	US 6,507,061	1/2003	Hudgens et al.		
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	AY6	US 6,576,921	6/2003	Lowery		
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	AB7	US 6,590,807	7/2003	Lowery		
	AC7	US 6,593,176	7/2003	Dennison		
	AD7	US 6,597,009	7/2003	Wicker		
	AE7	US 6,605,527	8/2003	Dennison et al.		
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Sheet 5 of 13

Complete if Known	
Application Number	10/796,111
Filing Date	March 10, 2004
First Named Inventor	Dean A. Klein
Art Unit	2818
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0959/P0959

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	AK7	US 6,649,928	11/2003	Dennison	
	AJ7	US 6,667,900	12/2003	Lowery et al.	
	AM7	US 6,671,710	12/2003	Ovshinsky et al.	
	AN7	US 6,673,700	1/2004	Dennison et al.	
	AO7	US 6,674,115	1/2004	Hudgens et al.	
	AP7	US 6,687,427	2/2004	Ramalingam et al.	
	AQ7	US 6,690,026	2/2004	Peterson	
	AR7	US 6,696,355	2/2004	Dennison	
	AS7	US 6,687,153	2/2004	Lowery	
	AT7	US 6,707,712	3/2004	Lowery	
V	AU7	US 6,714,954	3/2004	Ovshinsky et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]-Number[4]-Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
pl	BA	JP-56126916	10/1981	Akira et al.		
p2	BB	WO 97/48032	12/18/1997	Kozicki et al.		
p2	BC	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	Pho M. Luu	Date Considered	10/28/04

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 6 of 13

Complete If Known	
Application Number	10/618,824 796-111
Filing Date	July 14, 2003
First Named Inventor	Terry L. Gilton
Group Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.1006/P1006-A

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
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	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
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	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
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	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
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First Named Inventor	Terry L. Gilton
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 12 of 13

Complete if Known	
Application Number	10/~~618,824~~ 796 - 111
Filing Date	July 14, 2003
First Named Inventor	Terry L. Gilton
Group Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.1006/P1006-A

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	CS5	Snell, A.J.; Lecomber, P.G.; Hajto, J.; Rose, M.J.; Owen, A.E.; Osborne, I.L., Analogue memory effects in metal/a-Si:H/metal memory devices, J. Non-Cryst. Solids 137-138 (1991) 1257-1262.	
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pl	CI6	Viger, C.; Lefrancois, G.; Fleury, G., Anomalous behaviour of amorphous selenium films, J. Non-Cryst. Solids 33 (1976) 267-272.	
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Examiner Signature	PHo M. Luu	Date Considered	10/28/04

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